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Docket: 140819-605  
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27 JUL 2001  
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re National Phase Patent Application of )  
Gaku SUGAHARA et al. )  
International Application No. PCT/JP00/08461 ) Attn: US/DO/EO  
International Filing Date: November 29, 2000 )  
For: SEMICONDUCTOR LASER DEVICE, )  
METHOD FOR FABRICATING THE )  
SAME, AND OPTICAL DISK APPARATUS ) Date: July 27, 2001

PRELIMINARY AMENDMENT

Honorable Commissioner for Patents  
Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows: Please note that specification is presented below in its amended form. It is further presented as an Attachment to the Amendment whereby the amendments to the specification are outlined using the conventional method of bracketing and underlining.

Please replace page 13, paragraph 3 as follows:

However, in the first embodiment, niobium oxide is used for the high-refractive-index film 13b of the end facet reflective film 13, and the light absorption coefficient of niobium oxide is lower than that of titanium oxide. Thus, a rise in temperature in the vicinity of the end facet of the resonant cavity 12 can be suppressed. As a result, the crystallinity of the quantum well active layer 1 and the